

FEATURES

- Near Infrared Reduced Footprint Photodiode
- Photosensitive Active Area: 0.86 mm x 0.86 mm
- High Sensitivity: 0.65 A/W ($\lambda = 850$ nm)
- Wide Operating Temperature: -40°C to +110°C
- Ideal for High Volume Laser Monitoring Applications
- RoHS and REACH Compliant

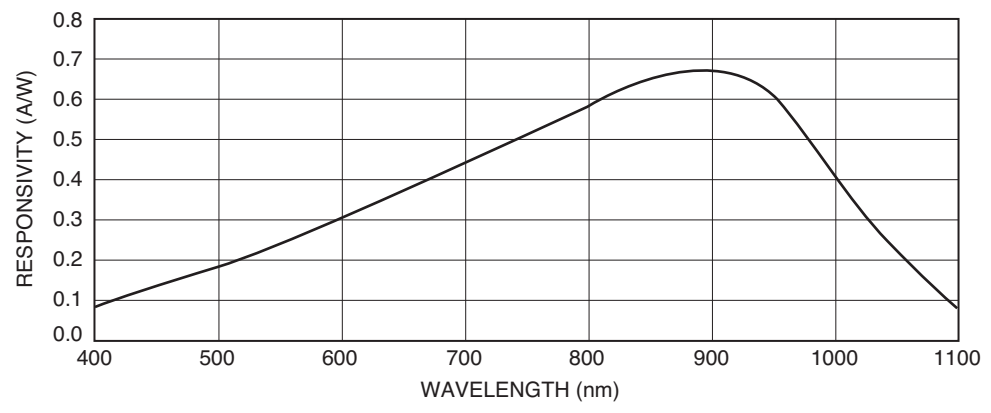
Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area			0.74		mm ²
Responsivity	@ 850 nm		0.65		A/W
Dark Current, I _{dr}	V _r = 3 V		0.1	0.75	nA
Shunt Resistance	V _R = 10 mV	200	800		M Ω
Reverse Breakdown Voltage, V _R	I _R = 10 μ A	25			Volts
Capacitance, C	V _R = 0 V			8	pF
Rise Time	V _R = 10 V		8	15	nsec

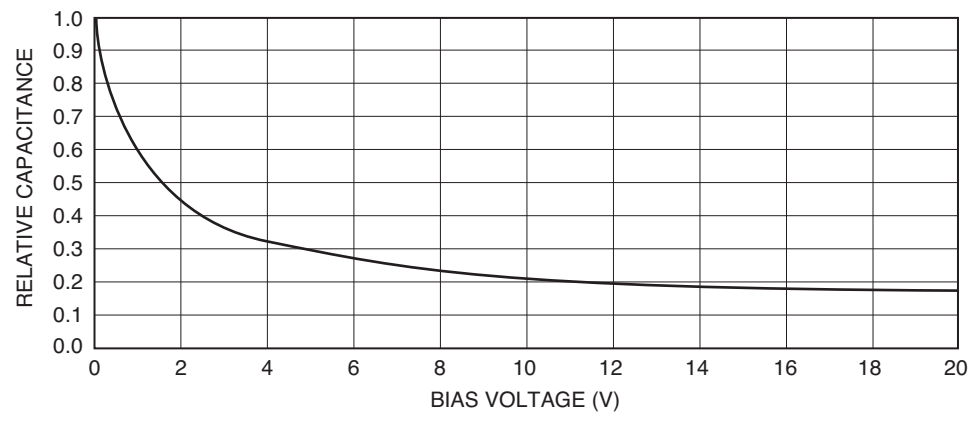
Thermal Parameters

Parameters	Units
Storage and Operating Temperature Range	-40°C to 110°C
Maximum Junction Temperature	110°C

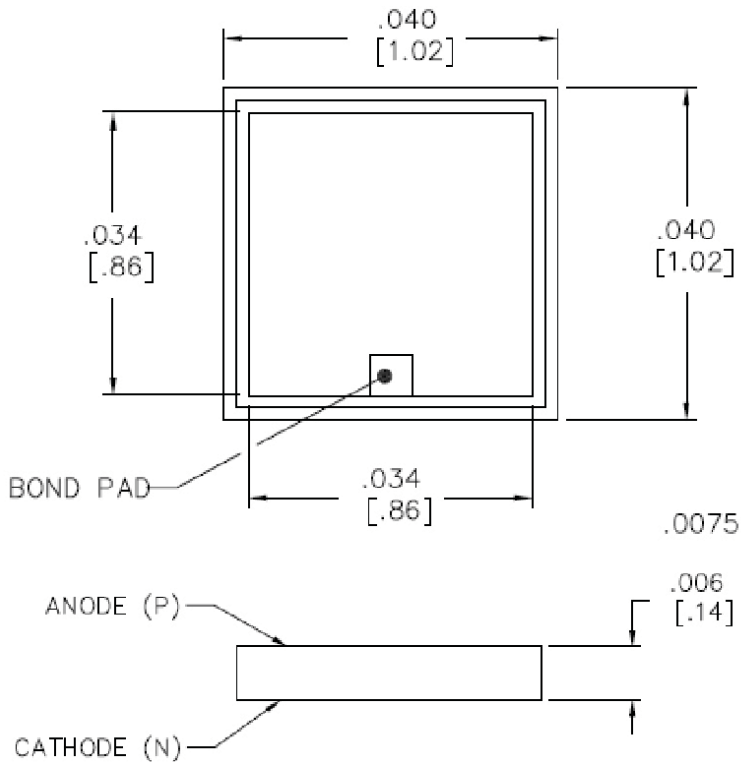
Typical Spectral Response



Capacitance vs Bias Voltage



Package Dimensions



Specifications are subject to change without prior notice.

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